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Applications of "[Embedded - Microcontrollers](#)"

Details

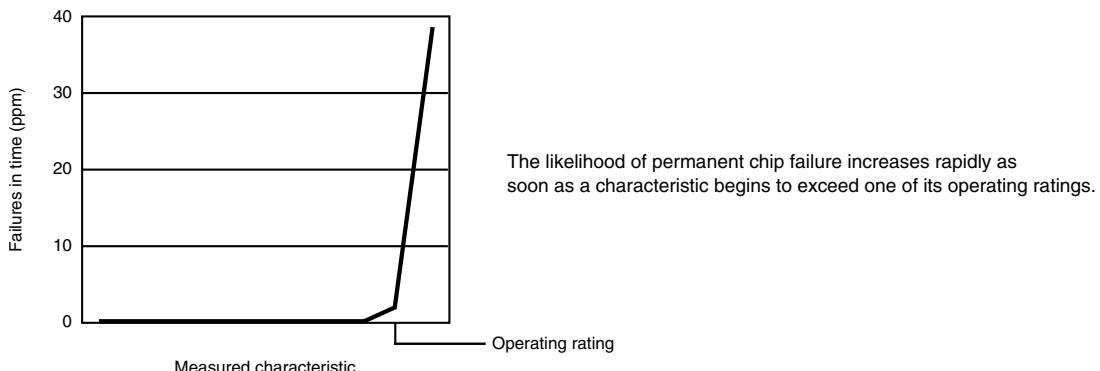
Product Status	Active
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	EBI/EMI, I ² C, SPI, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 19x12b; D/A 1x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcf51qu128vlhr

3.4.1 Example

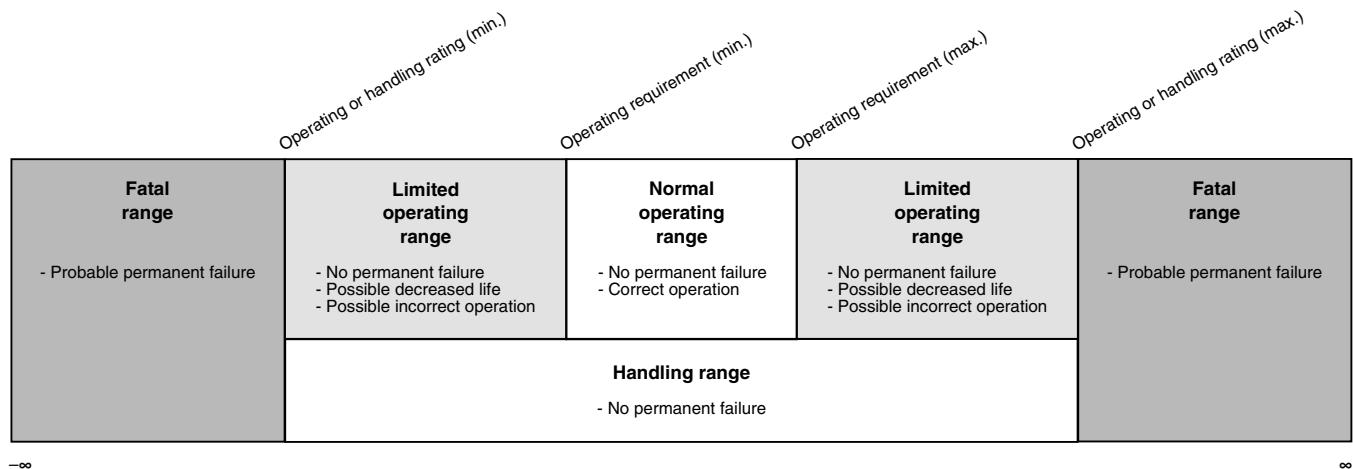
This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	-0.3	1.2	V

3.5 Result of exceeding a rating



3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.

5.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength • $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$, $I_{OH} = -9 \text{ mA}$	$V_{DD} - 0.5$	—	V	
	• $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$, $I_{OH} = -3 \text{ mA}$	$V_{DD} - 0.5$	—	V	
V_{OL}	Output low voltage — low drive strength • $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$, $I_{OL} = -2 \text{ mA}$	$V_{DD} - 0.5$	—	V	
	• $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$, $I_{OL} = -0.6 \text{ mA}$	$V_{DD} - 0.5$	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — high drive strength • $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$, $I_{OL} = 9 \text{ mA}$	—	0.5	V	
	• $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$, $I_{OL} = 3 \text{ mA}$	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
	Input leakage current (per pin) • @ full temperature range • @ 25°C	—	1.0	μA	1
I_{IN}		—	0.1	μA	
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
I_{OZ}	Total Hi-Z (off-state) leakage current (all input pins)	—	4	μA	
R_{PU}	Internal pullup resistors	22	50	$\text{k}\Omega$	2
R_{PD}	Internal pulldown resistors	22	50	$\text{k}\Omega$	3

1. Tested by ganged leakage method

2. Measured at $V_{input} = V_{SS}$ 3. Measured at $V_{input} = V_{DD}$

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx-RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 50 MHz
- Bus clock (and flash and Mini-FlexBus clocks) = 25 MHz

5. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash memory.
6. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks enabled, but peripherals are not in active operation. Code executing from flash memory.
7. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks disabled.
8. OSC clocks disabled.
9. All pads disabled.
10. Data reflects devices with 32 KB of RAM. For devices with 16 KB of RAM, power consumption is reduced by 500 nA. For devices with 8 KB of RAM, power consumption is reduced by 750 nA.
11. RTC function current includes LPTMR with OSC enabled with 32.768 kHz crystal at 3.0 V

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode, except for 50 MHz core (FEI mode)
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL
- For the ALLON curve, all peripheral clocks are enabled, but peripherals are not in active operation
- Voltage Regulator disabled
- No GPIOs toggled
- Code execution from flash memory with cache enabled

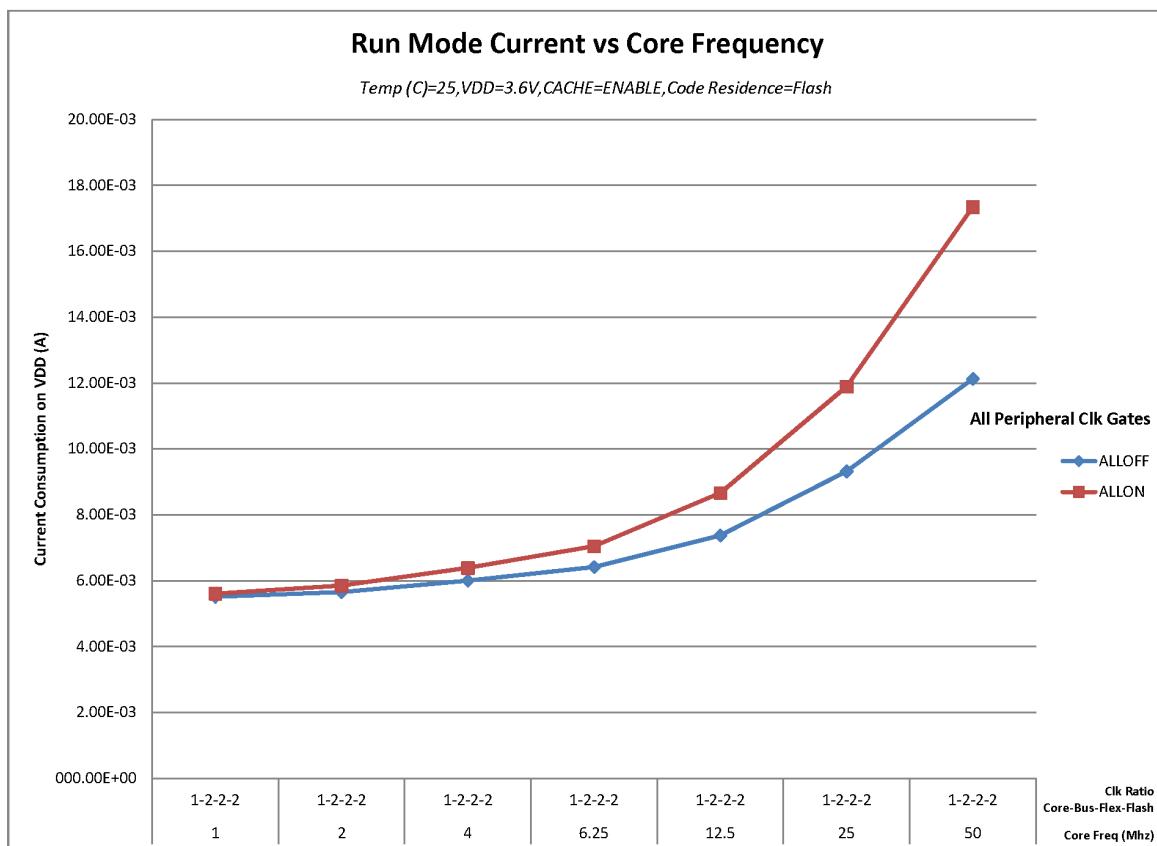


Figure 1. Run mode supply current vs. core frequency

5.3.1 General Switching Specifications

These general purpose specifications apply to all signals configured for EGPIO, MTIM, CMT, PDB, IRQ, and I²C signals. The conditions are 50 pF load, V_{DD} = 1.71 V to 3.6 V, and full temperature range. The GPIO are set for high drive, no slew rate control, and no input filter, digital or analog, unless otherwise specified.

Table 9. EGPIO General Control Timing

Symbol	Description	Min.	Max.	Unit
G1	Bus clock from CLK_OUT pin high to GPIO output valid	—	32	ns
G2	Bus clock from CLK_OUT pin high to GPIO output invalid (output hold)	1	—	ns
G3	GPIO input valid to bus clock high	28	—	ns
G4	Bus clock from CLK_OUT pin high to GPIO input invalid	—	4	ns
	GPIO pin interrupt pulse width (digital glitch filter disabled) Synchronous path ¹	1.5	—	Bus clock cycles
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) Asynchronous path ²	100	—	ns
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) Asynchronous path ²	50	—	ns
	External reset pulse width (digital glitch filter disabled)	100	—	ns
	Mode select (MS) hold time after reset deassertion	2	—	Bus clock cycles

1. The greater synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.

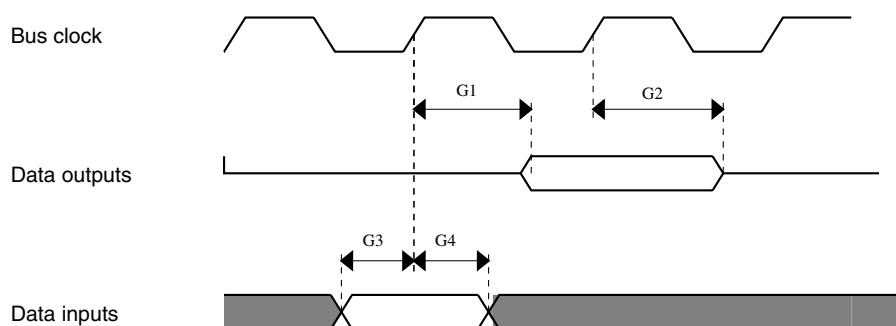


Figure 3. EGPIO timing diagram

Table 14. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$f_{dco_t_DMX3}$ 2	DCO output frequency Low range (DRS=00) $732 \times f_{fill_ref}$	—	23.99	—	MHz	4, 5
		—	47.97	—	MHz	
		—	71.99	—	MHz	
		—	95.98	—	MHz	
J_{cyc_fill}	FLL period jitter • $f_{VCO} = 48$ MHz • $f_{VCO} = 98$ MHz	—	180	—	ps	
		—	150	—	ps	
$t_{fill_acquire}$	FLL target frequency acquisition time	—	—	1	ms	6
PLL						
f_{VCO}	VCO operating frequency	48.0	—	100	MHz	
I_{PLL}	PLL operating current • PLL @ 96 MHz ($f_{osc_hi_1} = 8$ MHz, $f_{PLL_ref} = 2$ MHz, VDIV multiplier = 48)	—	1060	—	μA	7
I_{PLL}	PLL operating current • PLL @ 48 MHz ($f_{osc_hi_1} = 8$ MHz, $f_{PLL_ref} = 2$ MHz, VDIV multiplier = 24)	—	600	—	μA	7
f_{PLL_ref}	PLL reference frequency range	2.0	—	4.0	MHz	
J_{cyc_PLL}	PLL period jitter (RMS) • $f_{VCO} = 48$ MHz • $f_{VCO} = 100$ MHz	—	120	—	ps	8
		—	50	—	ps	
J_{acc_PLL}	PLL accumulated jitter over 1μs (RMS) • $f_{VCO} = 48$ MHz • $f_{VCO} = 100$ MHz	—	1350	—	ps	8
		—	600	—	ps	
D_{lock}	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	
D_{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t_{PLL_lock}	Lock detector detection time	—	—	150×10^{-6} + $1075(1/f_{PLL_ref})$	s	9

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
3. The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature should be considered.
4. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
5. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.

Table 15. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)					
	• 1 MHz resonator	—	6.6	—	kΩ	
	• 2 MHz resonator	—	3.3	—	kΩ	
	• 4 MHz resonator	—	0	—	kΩ	
	• 8 MHz resonator	—	0	—	kΩ	
	• 16 MHz resonator	—	0	—	kΩ	
V_{pp}^5	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. $V_{DD}=3.3$ V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x, C_y can be provided by using either the integrated capacitors or by using external components.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

Table 17. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk32k}$	Erase Block high-voltage time for 32 KB	—	52	452	ms	1
$t_{hversblk128k}$	Erase Block high-voltage time for 128 KB	—	208	1808	ms	1

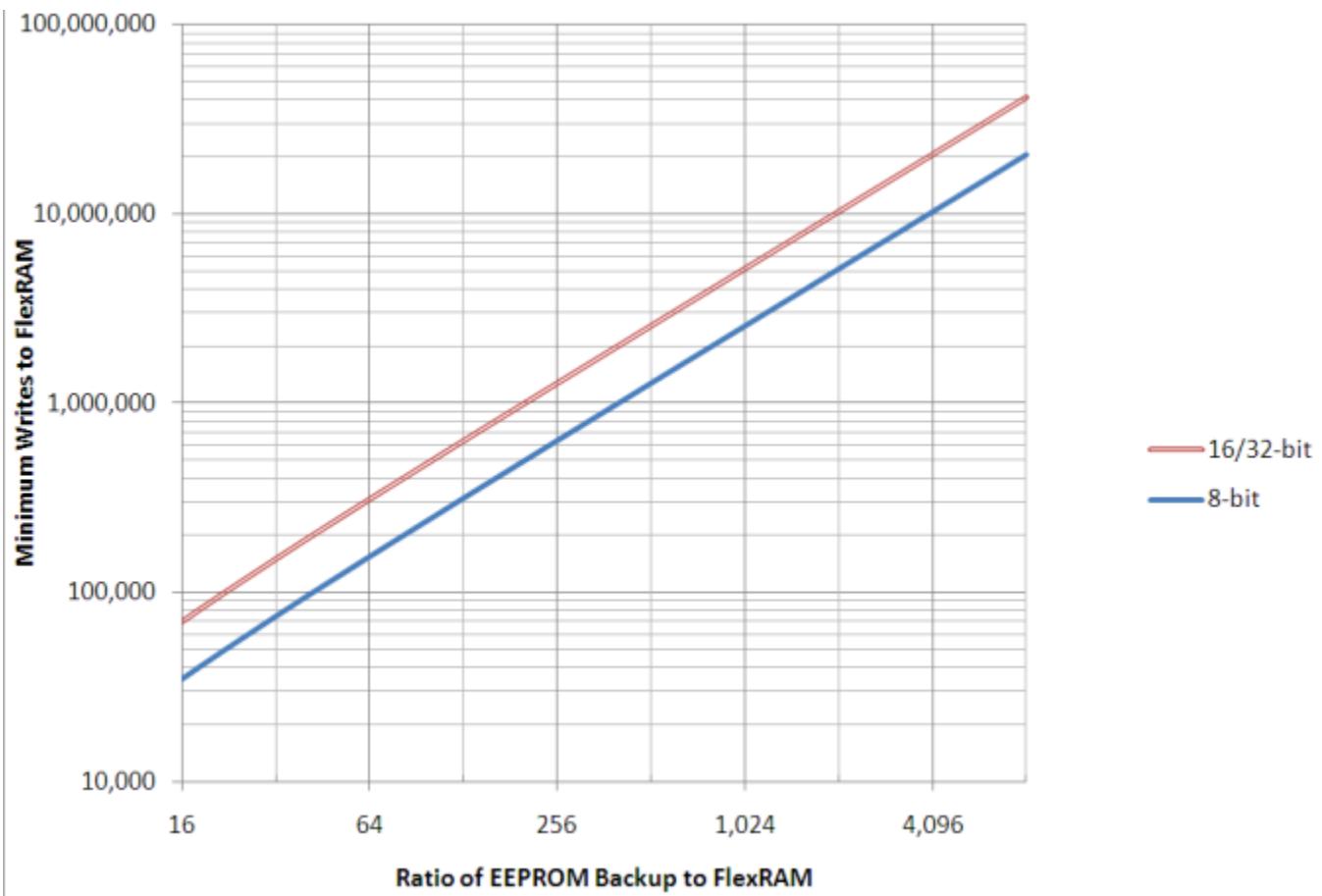
1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 18. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk32k}$	Read 1s Block execution time • 32 KB data flash	—	—	0.5	ms	
$t_{rd1blk128k}$	• 128 KB program flash	—	—	1.7	ms	
$t_{rd1sec1k}$	Read 1s Section execution time (data flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	
$t_{ersblk32k}$	Erase Flash Block execution time • 32 KB data flash	—	55	465	ms	2
$t_{ersblk128k}$	• 128 KB program flash	—	220	1850	ms	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
$t_{pgmsec512}$	Program Section execution time • 512 B flash	—	4.7	—	ms	
$t_{pgmsec1k}$	• 1 KB flash	—	9.3	—	ms	
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	
t_{ersall}	Erase All Blocks execution time	—	275	2350	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
$t_{pgmpart32k}$	Program Partition for EEPROM execution time • 32 KB FlexNVM	—	70	—	ms	

Table continues on the next page...

**Figure 5. EEPROM backup writes to FlexRAM**

6.4.2 EzPort Switching Specifications

All timing is shown with respect to a maximum pin load of 50 pF and input signal transitions of 3 ns.

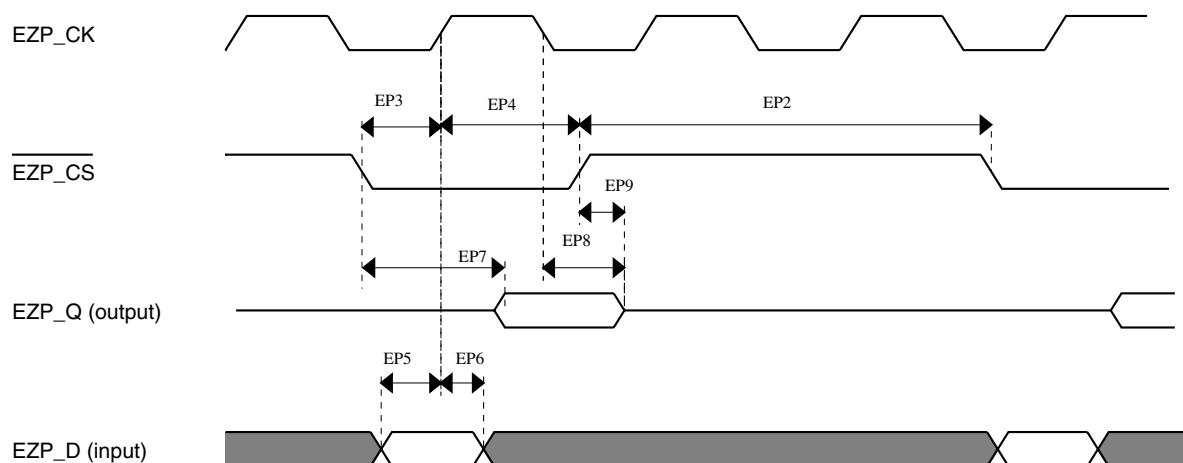
Table 21. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{SYS}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{SYS}/8$	MHz
EP2	EZP_CS negation to next EZP_CS assertion	$2 \times t_{EZP_CK}$	—	ns
EP3	EZP_CS input valid to EZP_CK high (setup)	15	—	ns
EP4	EZP_CK high to EZP_CS input invalid (hold)	0.0	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	15	—	ns

Table continues on the next page...

Table 21. EzPort switching specifications (continued)

Num	Description	Min.	Max.	Unit
EP6	EZP_CK high to EZP_D input invalid (hold)	0.0	—	ns
EP7	EZP_CK low to EZP_Q output valid (setup)	—	25	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0.0	—	ns
EP9	EZP_CS negation to EZP_Q tri-state	—	12	ns

**Figure 6. EzPort Timing Diagram**

6.4.3 Mini-Flexbus Switching Specifications

All processor bus timings are synchronous; input setup/hold and output delay are given in respect to the rising edge of a reference clock, FB_CLK. The FB_CLK frequency may be the same as the internal system bus frequency or an integer divider of that frequency.

The following timing numbers indicate when data is latched or driven onto the external bus, relative to the Mini-Flexbus output clock (FB_CLK). All other timing relationships can be derived from these values.

Table 22. Flexbus switching specifications

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	
	Frequency of operation	—	25	MHz	
FB1	Clock period	40	—	ns	

Table continues on the next page...

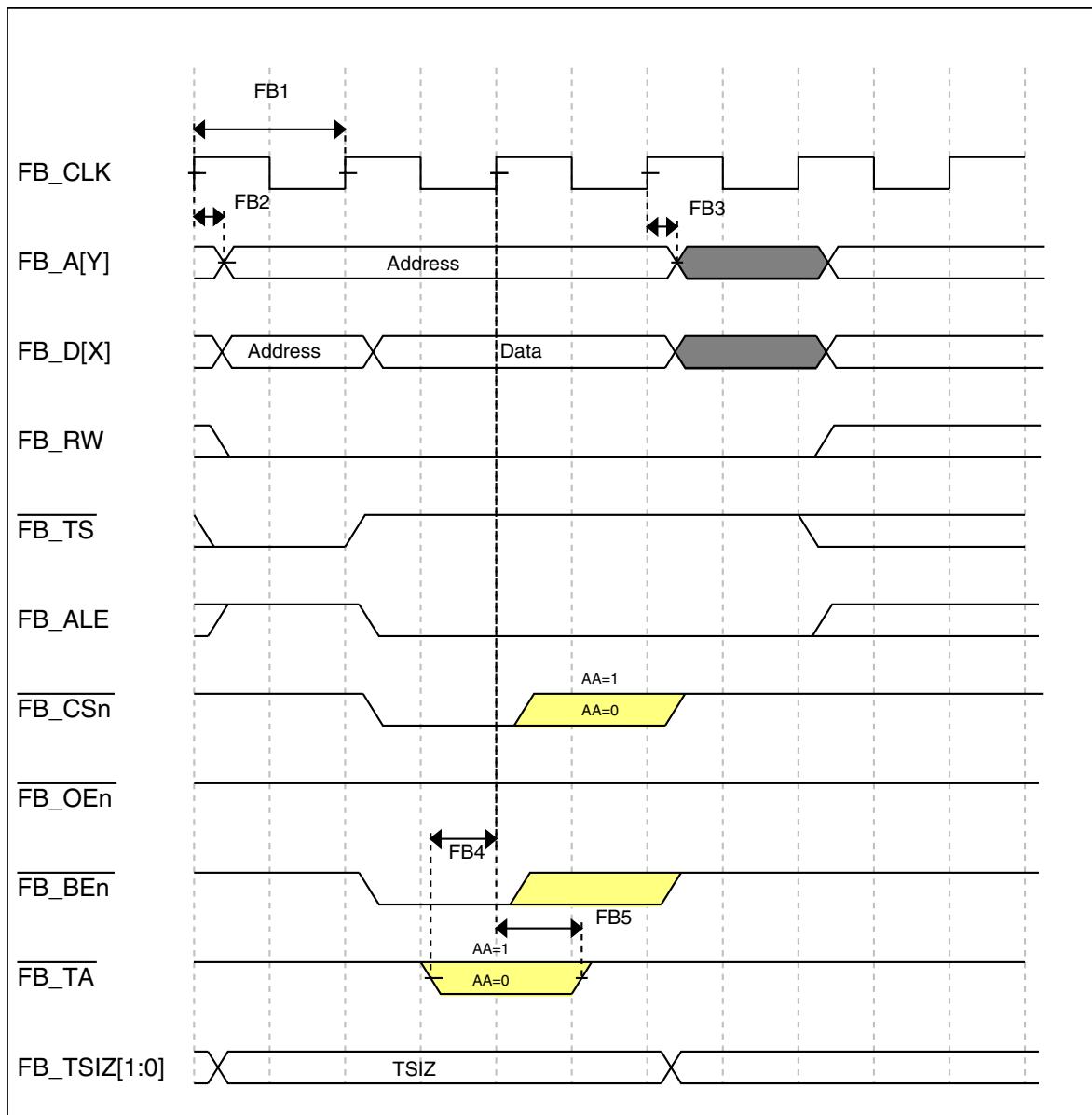


Figure 8. Mini-FlexBus write timing diagram

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

All ADC channels meet the 12-bit single-ended accuracy specifications.

6.6.1.1 12-bit ADC operating conditions

Table 23. 12-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} - V_{DDA}$)	-100	0	+100	mV	²
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} - V_{SSA}$)	-100	0	+100	mV	²
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	Reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
C_{ADIN}	Input capacitance	• 8/10/12 bit modes	— —	4	5	pF	
R_{ADIN}	Input resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance	12 bit modes $f_{ADCK} < 4\text{MHz}$	—	—	5	kΩ	³
f_{ADCK}	ADC conversion clock frequency	≤ 12 bit modes	1.0	—	18.0	MHz	⁴
C_{rate}	ADC conversion rate	≤ 12 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	⁵

1. Typical values assume $V_{DDA} = 3.0$ V, Temp = 25°C , $f_{ADCK} = 1.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. The analog source resistance should be kept as low as possible in order to achieve the best results. The results in this datasheet were derived from a system which has $<8 \Omega$ analog source resistance. The R_{AS}/C_{AS} time constant should be kept to $<1\text{ns}$.
4. To use the maximum ADC conversion clock frequency, the ADHSC bit should be set and the ADLPC bit should be clear.

6.8 Communication interfaces

6.8.1 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

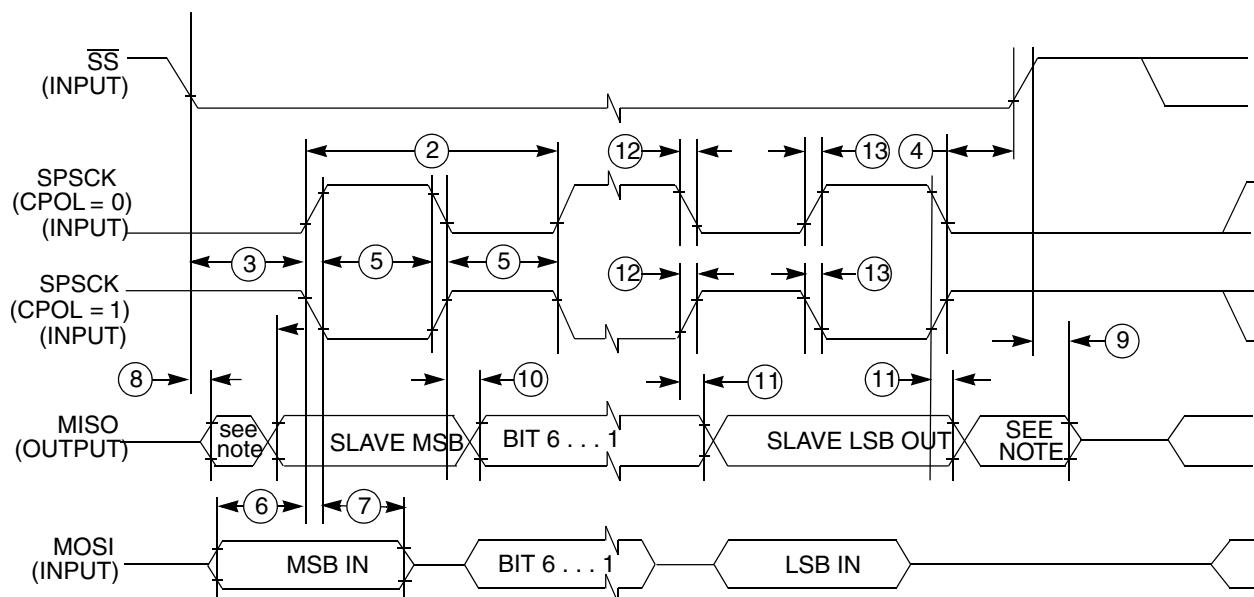
All timing is shown with respect to 20% V_{DD} and 70% V_{DD} , unless noted, as well as input signal transitions of 3 ns and a 50 pF maximum load on all SPI pins. All timing assumes slew rate control is disabled and high drive strength is enabled for SPI output pins.

Table 32. SPI master mode timing

Num.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	$f_{BUS}/2048$	$f_{BUS}/2$	Hz	f_{BUS} is the bus clock as defined in Table 8 .
2	t_{SPSCK}	SPSCK period	$2 \times t_{BUS}$	$2048 \times t_{BUS}$	ns	$t_{BUS} = 1/f_{BUS}$
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{wSPSCK}	Clock (SPSCK) high or low time	$t_{BUS} - 30$	$1024 \times t_{BUS}$	ns	—
6	t_{su}	Data setup time (inputs)	21	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	25	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	$t_{BUS} - 25$	ns	—
	t_{FI}	Fall time input	—			
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output	—			

Table 33. SPI slave mode timing (continued)

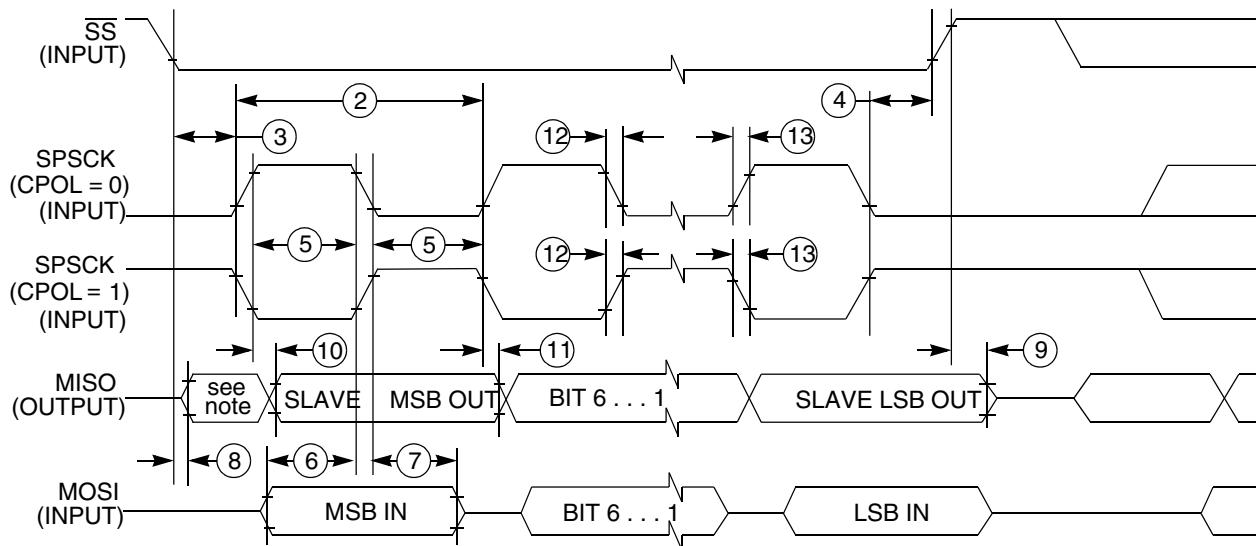
Num.	Symbol	Description	Min.	Max.	Unit	Comment
2	t_{SPSCK}	SPSCK period	$4 \times t_{BUS}$	—	ns	$t_{BUS} = 1/f_{BUS}$
3	t_{Lead}	Enable lead time	1	—	t_{BUS}	—
4	t_{Lag}	Enable lag time	1	—	t_{BUS}	—
5	t_{wSPSCK}	Clock (SPSCK) high or low time	$t_{BUS} - 30$	—	ns	—
6	t_{SU}	Data setup time (inputs)	19.5	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_a	Slave access time	—	t_{BUS}	ns	Time to data active from high-impedance state
9	t_{dis}	Slave MISO disable time	—	t_{BUS}	ns	Hold time to high-impedance state
10	t_v	Data valid (after SPSCK edge)	—	27	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	$t_{BUS} - 25$	ns	—
	t_{FI}	Fall time input	—	—	—	—
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output	—	—	—	—



NOTE: Not defined!

Figure 16. SPI slave mode timing (CPHA=0)

Human-machine interfaces (HMI)



NOTE: Not defined!

Figure 17. SPI slave mode timing (CPHA=1)

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 34. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DDTSI}	Operating voltage	1.71	—	3.6	V	
C_{ELE}	Target electrode capacitance range	1	20	500	pF	1
f_{REFmax}	Reference oscillator frequency	—	5.5	14	MHz	2
$f_{ELEMmax}$	Electrode oscillator frequency	—	0.5	4.0	MHz	3
C_{REF}	Internal reference capacitor	0.5	1	1.2	pF	
V_{Δ}	Oscillator delta voltage	100	600	760	mV	4
I_{REF}	Reference oscillator current source base current • 1uA setting (REFCHRG=0) • 32uA setting (REFCHRG=31)	—	1.133 36	1.5 50	µA	3, 5
I_{ELE}	Electrode oscillator current source base current • 1uA setting (EXTCHRG=0) • 32uA setting (EXTCHRG=31)	—	1.133 36	1.5 50	µA	3, 6
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	%	7
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	%	8
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	%	9
MaxSens	Maximum sensitivity	0.003	12.5	—	fF/count	10

Table continues on the next page...

8 Pinout

8.1 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Mux Control module is responsible for selecting which ALT functionality is available on each pin.

NOTE

- On PTB0, EZP_MS_b is active only during reset. Refer to the detailed boot description.
- PTC1 is open drain.

64-pin	48-pin	44-pin	32-pin	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
1	—	—	—	VDD	VDD								
2	—	—	—	VSS	VSS								
3	—	—	—	Disabled	Disabled	PTC6	UART0_TX	I2C0_SCL	GPIO6	SPI1_MOSI	FBa_AD11		
4	—	—	—	Disabled	Disabled	PTC7	UART0_RX	I2C0_SDA	GPIO7	SPI1_MISO	FBa_AD12		
5	1	—	—	Disabled	Disabled	PTD0	UART0_CT_S_b	I2C1_SDA	GPIO8	SPI1_SCLK	FBa_AD13		
6	2	—	—	Disabled	Disabled	PTD1	UART0_RT_S_b	I2C1_SCL	GPIO9	SPI1_SS	FBa_AD14		
7	3	1	1	Disabled	Disabled	PTA0		I2C2_SCL	FTM1_CH0	SPI0_SS	FBa_AD15		
8	4	2	2	Disabled	Disabled	PTA1		I2C2_SDA	FTM1_CH1		FBa_AD16		
9	5	3	3	Disabled	Disabled	PTA2	UART1_TX		FTM1_CH2	SPI1_SS			
10	6	4	4	Disabled	Disabled	PTA3	UART1_RX		FTM1_CH3	SPI1_SCLK			EZP_CLK
11	7	5	5	ADC0_SE2	ADC0_SE2	PTA4	UART1_CT_S_b	I2C2_SCL	FTM1_CH4	SPI1_MISO			EZP_DI
12	8	6	6	ADC0_SE3	ADC0_SE3	PTA5	UART1_RT_S_b	I2C2_SDA	FTM1_CH5	SPI1_MOSI	CLKOUT		EZP_DO
13	9	7	7	VDDA	VDDA								
14	10	8	—	VREFH	VREFH								
15	11	9	—	VREF_OUT	VREF_OUT								
16	12	10	—	VREFL	VREFL								
17	13	11	8	VSSA	VSSA								
18	14	12	9	DAC0_OUT	DAC0_OUT								
19	15	13	10	ADC0_SE0	ADC0_SE0								
20	16	14	11	ADC0_SE1	ADC0_SE1								
21	17	15	12	VREGIN	VREGIN								
22	18	16	13	VOUT33	VOUT33								
23	19	17	14	VSS	VSS								

64-pin	48-pin	44-pin	32-pin	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
24	20	18	—	VDD	VDD								
25	21	19	15	ADC0_SE8/ TSI0_CH0	ADC0_SE8/ TSI0_CH0	PTA6		LPTMR_AL T1	FTM_FLT1	FBa_D7	FBa_AD17		
26	—	—	—	ADC0_SE9/ TSI0_CH1	ADC0_SE9/ TSI0_CH1	PTD2	FTM0_QD_ PHA	GPIO10	FTM0_CH0				
27	22	20	—	ADC0_SE1 0/TSI0_CH2	ADC0_SE1 0/TSI0_CH2	PTD3	FTM0_QD_ PHB	GPIO11	FTM0_CH1	FBa_D6	FBa_AD0		
28	—	—	—	ADC0_SE1 1/TSI0_CH3	ADC0_SE1 1/TSI0_CH3	PTD4		GPIO12			FBa_D7		
29	—	—	—	ADC0_SE1 2/TSI0_CH4	ADC0_SE1 2/TSI0_CH4	PTD5		GPIO13			FBa_D6		
30	23	21	16	ADC0_SE1 3/TSI0_CH5	ADC0_SE1 3/TSI0_CH5	PTA7	UART0_TX		FTM0_QD_ PHA		FBa_D5		
31	24	22	—	ADC0_SE1 4/TSI0_CH6	ADC0_SE1 4/TSI0_CH6	PTD6	UART0_RX	GPIO14			FBa_D4		
32	—	—	—	ADC0_SE1 5/TSI0_CH7	ADC0_SE1 5/TSI0_CH7	PTD7	UART0_CT S_b	I2C3_SCL	GPIO15		FBa_D3		
33	—	—	—	TSI0_CH8	TSI0_CH8	PTE0	UART0_RT S_b	I2C3_SDA			FBa_D2		
34	—	—	—	TSI0_CH9	TSI0_CH9	PTE1	SPI0_SS		FTM_FLT0		FBa_D1		
35	25	23	17	IRQ/ EZP_MS_b	Disabled	PTB0		I2C0_SCL		IRQ/ EZP_MS_b			EZP_CS_b
36	26	24	18	TSI0_CH10	TSI0_CH10	PTB1	SPI0_SCLK	I2C0_SDA	FTM_FLT2	LPTMR_AL T2	FTM0_QD_ PHB	FB_CLKOUT	
37	—	—	—	TSI0_CH11	TSI0_CH11	PTE2		I2C3_SCL			FBa_D0		
38	—	—	—	ADC0_SE1 6/ TSI0_CH12	ADC0_SE1 6/ TSI0_CH12	PTE3	SPI0_MOSI	I2C3_SDA			FBa_OE_b		
39	27	25	19	ADC0_SE1 7/ TSI0_CH13	ADC0_SE1 7/ TSI0_CH13	PTB2	SPI0_MISO				FBa_CS0_b		
40	28	26	20	ADC0_SE1 8/ TSI0_CH14	ADC0_SE1 8/ TSI0_CH14	PTB3	SPI0_MOSI			FBa_CS1_b	FBa_ALE		
41	29	—	—	ADC0_SE1 9/ TSI0_CH15	ADC0_SE1 9/ TSI0_CH15	PTE4	UART0_RT S_b	LPTMR_AL T3	SPI1_SS		FBa_AD1		
42	30	—	—	ADC0_SE2 0	ADC0_SE2 0	PTE5	UART0_CT S_b	I2C1_SCL	SPI1_SCLK		FBa_AD2		
43	—	—	—	ADC0_SE2 1	ADC0_SE2 1	PTE6	UART0_RX	I2C1_SDA	SPI1_MISO		FBa_AD3		
44	31	27	—	ADC0_SE2 2	ADC0_SE2 2	PTE7	UART0_TX	PDB0_EXT RG	SPI1_MOSI	FBa_RW_b	FBa_AD4		
45	32	28	21	BKGD/MS	Disabled	PTB4	BKGD/MS						
46	33	29	22	XTAL2	XTAL2	PTB5							
47	34	30	23	EXTAL2	EXTAL2	PTB6							
48	35	31	24	VDD	VDD								

Table 35. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
48	35	31	24		VDD
2					VSS
23	19	17	14		VSS
49	36	32	25		VSS
System					
45	32	28	21	PTB4	BKGD/MS
12	8	6	6	PTA5	CLKOUT
62	46	42	30	PTC3	CLKOUT
10	6	4	4	PTA3	EZP_CLK
11	7	5	5	PTA4	EZP_DI
12	8	6	6	PTA5	EZP_DO
35	25	23	17	PTB0	IRQ/EZP_MS_b, EZP_CS_b
52	39	35	28	PTC1	RESET_b
OSC					
50	37	33	26	PTB7	EXTAL1
47	34	30	23	PTB6	EXTAL2
51	38	34	27	PTC0	XTAL1
46	33	29	22	PTB5	XTAL2
LLWU					
4				PTC7	LLWU_P0
6	2			PTD1	LLWU_P1
12	8	6	6	PTA5	LLWU_P2
30	23	21	16	PTA7	LLWU_P3
32				PTD7	LLWU_P4
35	25	23	17	PTB0	LLWU_P5
36	26	24	18	PTB1	LLWU_P6
39	27	25	19	PTB2	LLWU_P7
44	31	27		PTE7	LLWU_P8
45	32	28	21	PTB4	LLWU_P9
55				PTF2	LLWU_P10
56	40	36		PTF3	LLWU_P11
57	41	37	29	PTC2	LLWU_P12
59	43	39		PTF5	LLWU_P13
62	46	42	30	PTC3	LLWU_P14

Table continues on the next page...

Table 35. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
11	7	5	5	PTA4	PTA4
12	8	6	6	PTA5	PTA5
25	21	19	15	PTA6	PTA6
30	23	21	16	PTA7	PTA7
PTB					
35	25	23	17	PTB0	PTB0
36	26	24	18	PTB1	PTB1
39	27	25	19	PTB2	PTB2
40	28	26	20	PTB3	PTB3
45	32	28	21	PTB4	PTB4
46	33	29	22	PTB5	PTB5
47	34	30	23	PTB6	PTB6
50	37	33	26	PTB7	PTB7
PTC					
51	38	34	27	PTC0	PTC0
52	39	35	28	PTC1	PTC1
57	41	37	29	PTC2	PTC2
62	46	42	30	PTC3	PTC3
63	47	43	31	PTC4	PTC4
64	48	44	32	PTC5	PTC5
3				PTC6	PTC6
4				PTC7	PTC7
PTD					
5	1			PTD0	PTD0
6	2			PTD1	PTD1
26				PTD2	PTD2
27	22	20		PTD3	PTD3
28				PTD4	PTD4
29				PTD5	PTD5
31	24	22		PTD6	PTD6
32				PTD7	PTD7
PTE					
33				PTE0	PTE0
34				PTE1	PTE1
38				PTE3	PTE2

Table continues on the next page...

Revision History

Table 35. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
44	31	27		PTE7	UART0_TX
64	48	44	32	PTC5	UART0_TX
UART1					
11	7	5	5	PTA4	UART1_CTS_b
58	42	38		PTF4	UART1_CTS_b
12	8	6	6	PTA5	UART1_RTS_b
57	41	37	29	PTC2	UART1_RTS_b
10	6	4	4	PTA3	UART1_RX
59	43	39		PTF5	UART1_RX
9	5	3	3	PTA2	UART1_TX
60	44	40		PTF6	UART1_TX

9 Revision History

The following table summarizes content changes since the previous release of this document.

Table 36. Revision History

Rev. No.	Date	Substantial Changes
4	01/2012	Thermal operating requirements: Changed maximum T_J value from 125°C to 115°C